

**IN74HC154A**

**1-of-16 Decoder/Demultiplexer  
High-Performance Silicon-Gate CMOS**

The IN74HC154A is identical in pinout to the LS/ALS154. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LS/ALSTTL outputs.

This device, when enabled, selects one of 16 active-low outputs. Two active-low Chip Selects are provided to facilitate the chip-select, demultiplexing, and cascading functions. When either Chip Select is high, all outputs are high. The demultiplexing function is accomplished by using the Address inputs to select the desired device output.

The IN74HC154A is primarily used for memory address decoding and data routing applications.

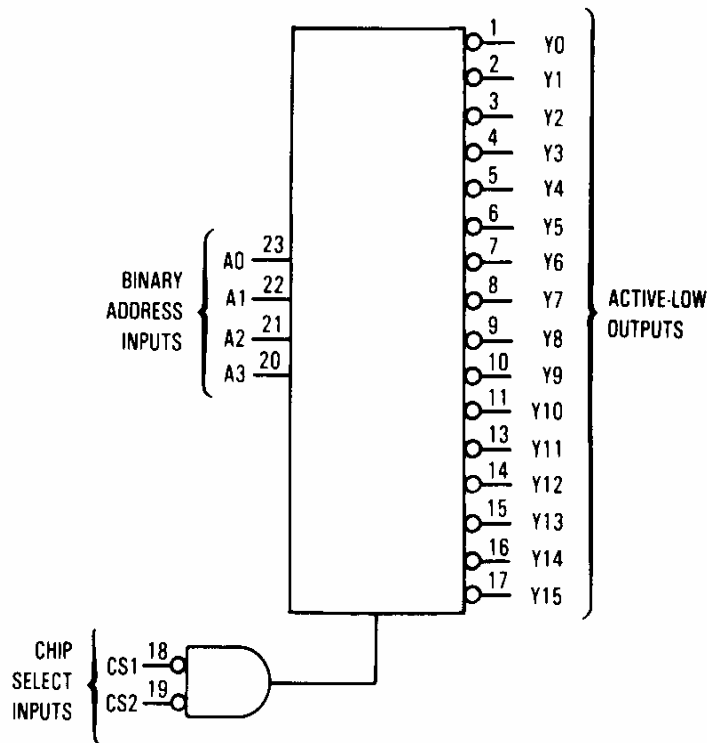
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0  $\mu$ A
- High Noise Immunity Characteristic of CMOS Devices

N SUFFIX  
PLASTIC

DW SUFFIX  
SOIC

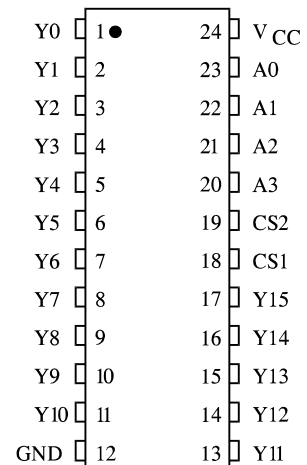
**ORDERING INFORMATION**  
IN74HC154AN Plastic  
IN74HC154ADW SOIC  
 $T_A = -55^\circ$  to  $125^\circ$  C for all packages

**LOGIC DIAGRAM**



PIN 24 =  $V_{CC}$   
PIN 12 = GND

**PIN ASSIGNMENT**



**MAXIMUM RATINGS\***

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	-0.5 to +7.0	V
V <sub>IN</sub>	DC Input Voltage (Referenced to GND)	-1.5 to V <sub>CC</sub> +1.5	V
V <sub>OUT</sub>	DC Output Voltage (Referenced to GND)	-0.5 to V <sub>CC</sub> +0.5	V
I <sub>IN</sub>	DC Input Current, per Pin	±20	mA
I <sub>OUT</sub>	DC Output Current, per Pin	±25	mA
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and GND Pins	±50	mA
P <sub>D</sub>	Power Dissipation in Still Air, Plastic DIP+ SOIC Package+	750 500	mW
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C
T <sub>L</sub>	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP or SOIC Package)	260	°C

\*Maximum Ratings are those values beyond which damage to the device may occur. Functional operation should be restricted to the Recommended Operating Conditions.

+Derating - Plastic DIP: - 10 mW/°C from 65° to 125°C

SOIC Package: - 7 mW/°C from 65° to 125°C

**RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	2.0	6.0	V
V <sub>IN</sub> , V <sub>OUT</sub>	DC Input Voltage, Output Voltage (Referenced to GND)	0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature, All Package Types	-55	+125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time (Figure 1)			ns
	V <sub>CC</sub> =2.0 V	0	1000	
	V <sub>CC</sub> =4.5 V	0	500	
	V <sub>CC</sub> =6.0 V	0	400	

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V<sub>IN</sub> and V<sub>OUT</sub> should be constrained to the range GND ≤ (V<sub>IN</sub> or V<sub>OUT</sub>) ≤ V<sub>CC</sub>.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V<sub>CC</sub>). Unused outputs must be left open.

## DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V <sub>CC</sub> V	Guaranteed Limit			Unit
				25 °C to -55°C	≤85 °C	≤125 °C	
V <sub>IH</sub>	Minimum High-Level Input Voltage	V <sub>OUT</sub> =0.1 V or V <sub>CC</sub> -0.1 V   I <sub>OUT</sub>   ≤ 20 μA	2.0	1.5	1.5	1.5	V
			4.5	3.15	3.15	3.15	
			6.0	4.2	4.2	4.2	
V <sub>IL</sub>	Maximum Low - Level Input Voltage	V <sub>OUT</sub> =0.1 V or V <sub>CC</sub> -0.1 V   I <sub>OUT</sub>   ≤ 20 μA	2.0	0.3	0.3	0.3	V
			4.5	0.9	0.9	0.9	
			6.0	1.2	1.2	1.2	
V <sub>OH</sub>	Minimum High-Level Output Voltage	V <sub>IN</sub> =V <sub>IH</sub> or V <sub>IL</sub>   I <sub>OUT</sub>   ≤ 20 μA	2.0	1.9	1.9	1.9	V
			4.5	4.4	4.4	4.4	
		6.0	5.9	5.9	5.9		
		V <sub>IN</sub> =V <sub>IH</sub> or V <sub>IL</sub>   I <sub>OUT</sub>   ≤ 4.0 mA   I <sub>OUT</sub>   ≤ 5.2 mA	4.5	3.98	3.84	3.7	
6.0	5.48	5.34	5.2				
V <sub>OL</sub>	Maximum Low-Level Output Voltage	V <sub>IN</sub> =V <sub>IH</sub> or V <sub>IL</sub>   I <sub>OUT</sub>   ≤ 20 μA	2.0	0.1	0.1	0.1	V
			4.5	0.1	0.1	0.1	
		6.0	0.1	0.1	0.1		
		V <sub>IN</sub> =V <sub>IH</sub> or V <sub>IL</sub>   I <sub>OUT</sub>   ≤ 4.0 mA   I <sub>OUT</sub>   ≤ 5.2 mA	4.5	0.26	0.33	0.4	
6.0	0.26	0.33	0.4				
I <sub>IN</sub>	Maximum Input Leakage Current	V <sub>IN</sub> =V <sub>CC</sub> or GND	6.0	±0.1	±1.0	±1.0	μA
I <sub>CC</sub>	Maximum Quiescent Supply Current (per Package)	V <sub>IN</sub> =V <sub>CC</sub> or GND I <sub>OUT</sub> =0μA	6.0	8.0	80	160	μA

**AC ELECTRICAL CHARACTERISTICS** ( $C_L=50\text{pF}$ , Input  $t_r=t_f=6.0\text{ ns}$ )

Symbol	Parameter	V <sub>CC</sub> V	Guaranteed Limit			Unit
			25 °C to -55°C	≤85°C	≤125°C	
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Input A to Output Y (Figures 1 and 3)	2.0	190	240	285	ns
		4.5	38	48	57	
		6.0	32	41	48	
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, CS to Output Y (Figures 2 and 3)	2.0	175	220	265	ns
		4.5	35	44	53	
		6.0	30	37	45	
t <sub>TLH</sub> , t <sub>THL</sub>	Maximum Output Transition Time, Any Output (Figures 2 and 3)	2.0	75	95	110	ns
		4.5	15	19	22	
		6.0	13	16	19	
C <sub>IN</sub>	Maximum Input Capacitance	-	10	10	10	pF

C <sub>PD</sub>	Power Dissipation Capacitance (Per Package)	Typical @25°C, V <sub>CC</sub> =5.0 V			pF
	Used to determine the no-load dynamic power consumption: $P_D=C_{PD}V_{CC}^2f+I_{CC}V_{CC}$	80			

**FUNCTION TABLE**

Inputs						Outputs																
CS1	CS2	A3	A2	A1	A0	Y0	Y1	Y2	Y3	Y4	Y5	Y6	Y7	Y8	Y9	Y10	Y11	Y12	Y13	Y14	Y15	
L	L	L	L	L	L	L	H	H	H	H	H	H	H	H	H	H	H	H	H	H	H	H
L	L	L	L	L	H	H	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L
L	L	L	L	H	L	H	H	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L
L	L	L	L	H	H	H	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L
L	L	L	H	L	L	H	H	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L
L	L	L	H	L	H	H	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L
L	L	L	H	H	L	H	H	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L
L	L	L	H	H	H	H	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L
L	L	H	L	L	L	H	H	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L
L	L	H	L	L	H	H	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L
L	L	H	L	H	L	H	H	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L
L	L	H	L	H	H	H	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L
L	L	H	H	L	L	H	H	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L
L	L	H	H	H	L	H	H	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L
L	L	H	H	H	H	H	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L
L	H	X	X	X	X	H	H	H	H	H	H	H	H	H	H	H	H	H	H	H	H	H
H	L	X	X	X	X	H	H	H	H	H	H	H	H	H	H	H	H	H	H	H	H	H
H	H	X	X	X	X	H	H	H	H	H	H	H	H	H	H	H	H	H	H	H	H	H

X = Don't Care

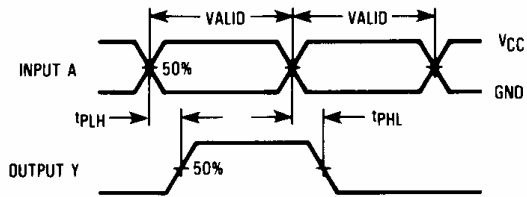


Figure 1. Switching Waveforms

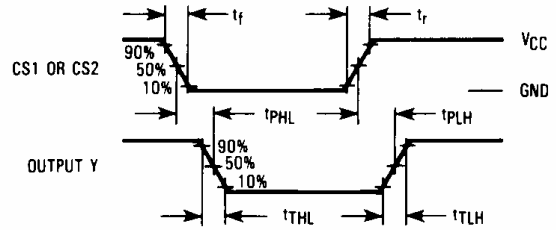
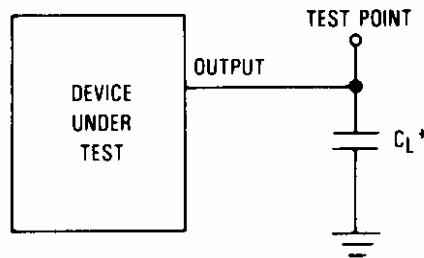


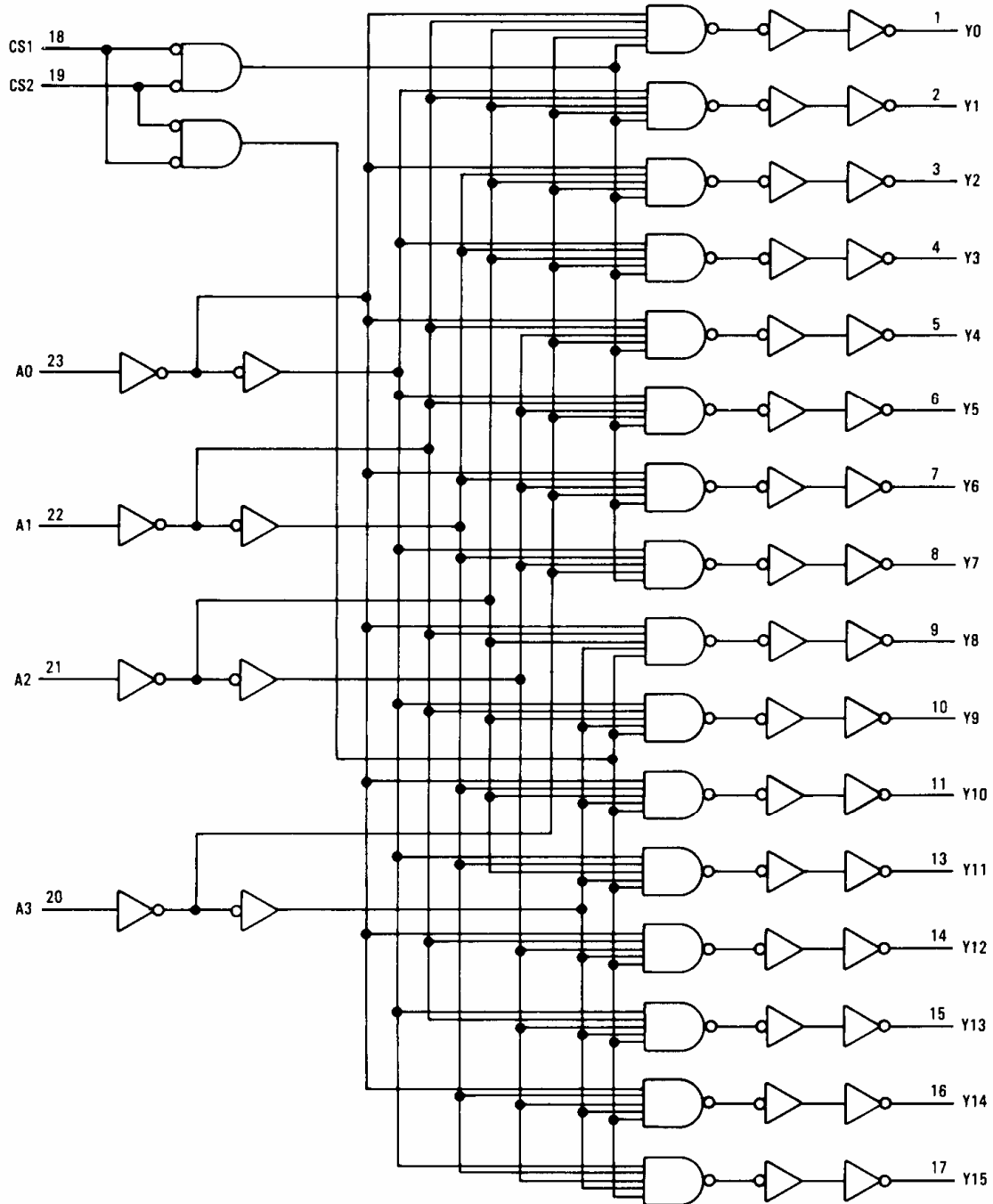
Figure 2. Switching Waveforms



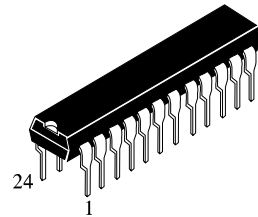
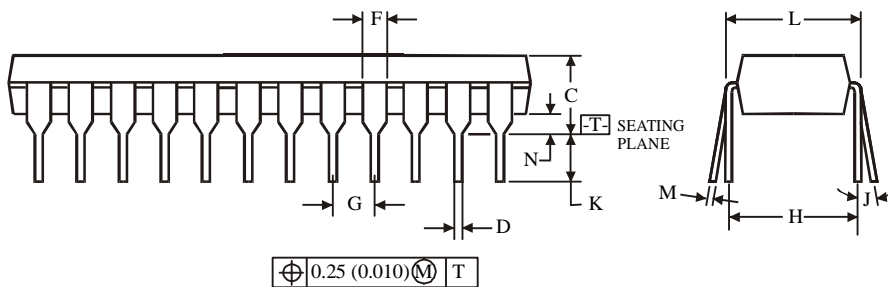
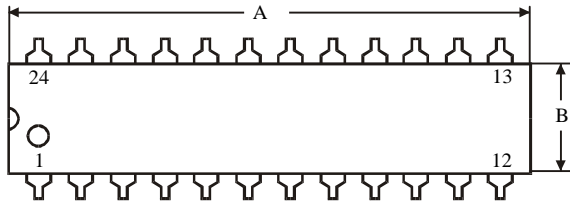
\*Includes all probe and jig capacitance.

Figure 3. Test Circuit

EXPANDED LOGIC DIAGRAM



**N SUFFIX PLASTIC DIP  
(MS - 001AF)**

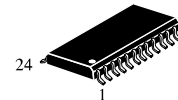
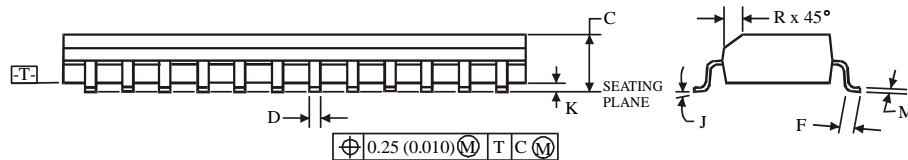
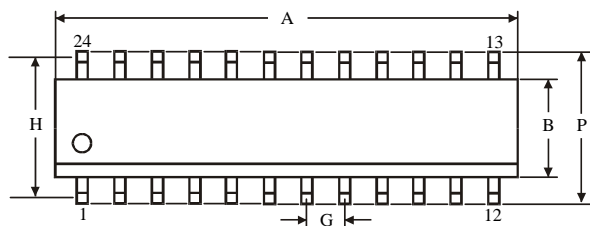


Symbol	Dimension, mm	
	MIN	MAX
A	31.24	32.51
B	6.1	7.11
C		5.33
D	0.36	0.56
F	1.14	1.78
G	2.54	
H	7.62	
J	0°	10°
K	2.92	3.81
L	7.62	8.26
M	0.2	0.36
N	0.38	

**NOTES:**

- Dimensions "A", "B" do not include mold flash or protrusions.  
Maximum mold flash or protrusions 0.25 mm (0.010) per side.

**D SUFFIX SOIC  
(MS - 013AD)**



Symbol	Dimension, mm	
	MIN	MAX
A	15.2	15.6
B	7.4	7.6
C	2.35	2.65
D	0.33	0.51
F	0.4	1.27
G	1.27	
H	9.53	
J	0°	8°
K	0.1	0.3
M	0.23	0.32
P	10	10.65
R	0.25	0.75

**NOTES:**

- Dimensions A and B do not include mold flash or protrusion.
- Maximum mold flash or protrusion 0.15 mm (0.006) per side for A; for B - 0.25 mm (0.010) per side.